TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

TCD2919BFG

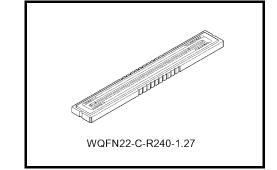


TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

TCD2919BFG

The TCD2919BFG is a high sensitive and low dark current 10680 elements \times 3 lines output CCD color linear image sensor with 10680 elements \times 1 line output CCD B/W linear image sensor.

The device contains a row of 10680 elements × 4 lines photodiodes which provide 48 lines/mm across a A4 size paper. The device is operated by 3.3 V pulse and 10 V power supply.



Features

• Number of Image Sensing Elements: 10680 elements \times 3 lines for Color

10680 elements × 1 line for B/W

• Image Sensing Element Size: 2.625 μ m by 8.4 μ m on 2.625 μ m center for Color 2.625 μ m by 8.4 μ m on 2.625 μ m center for B/W

· Photo Sensing Region: High sensitive PN photodiode

• Clock: 2-phase (3.3 V)

• Power Supply Voltage: 10 V (typ.)

Distanced between Photodiode Array: 31.5 μm (12 lines) R array – G array, G array – B array

63 μm (24 lines) B array - B/W array

Internal Circuit: Clamp circuit
Package: 22 pin CLCC
Color Filter: Red, Green, Blue

ABSOLUTE MAXIMUM RATINGS (Note 1)

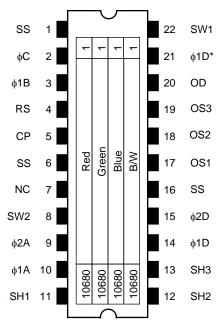
Characteristic	Symbol	Rating	Unit	
Clock pulse voltage	V_{ϕ}			
Shift pulse voltage	VsH			
Reset pulse voltage	V _{RS}	-0.3 to +8.0	V	
Clamp pulse voltage	V _{CP}			
Switch pulse voltage	Vsw			
Power supply voltage	V _{OD}	-0.3 to +13.5	V	
Operating temperature	T _{opr}	0 to 60	°C	
Storage temperature	T _{stg}	-25 to +85	°C	

Note 1: All voltages are with respect to SS terminals (ground).

None of the ABSOLUTE MAXIMUM RATINGS must be exceeded, even instantaneously.

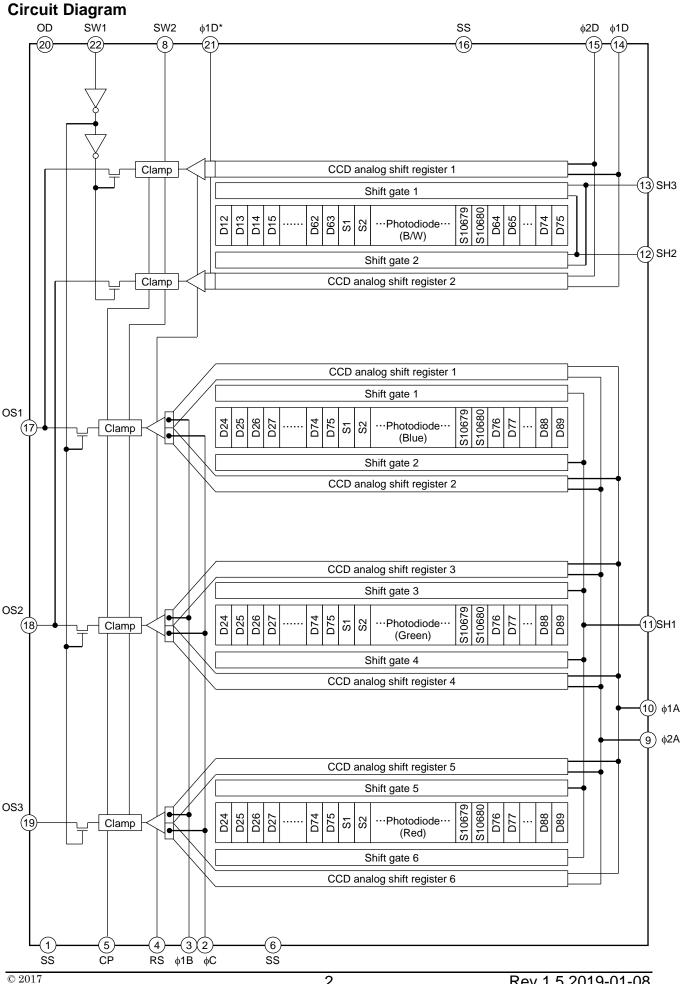
If any one of the ABSOLUTE MAXIMUM RATINGS is exceeded, the electrical characteristics, reliability and life time of the device cannot be guaranteed. If the ABSOLUTE MAXIMUM RATINGS are exceeded, the device can be permanently damaged or degraded. Create a system design in such a manner that any of the ABSOLUTE MAXIMUM RATINGS will not be exceeded under any circumstances.

Pin Connections (top view)



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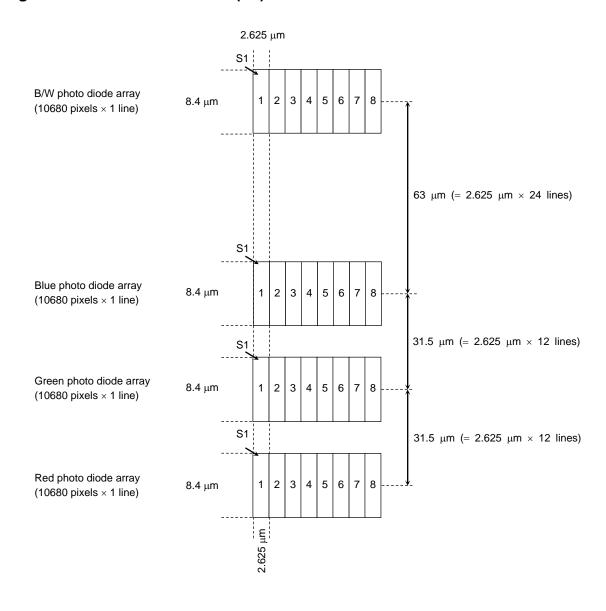
Rev.1.5 2019-01-08



Pin Names

Pin No.	Symbol	Name	Pin No.	Symbol	Name
1	SS	Ground	22	SW1	Switch gate 1 for color or B/W
2	φС	Last stage transfer clock for Color	21	φ1D*	Last stage transfer clock (phase 1) for B/W
3	φ1Β	Last stage transfer clock (phase 1) for color	20	OD	Power
4	RS	Reset gate	19	OS3	Output signal 3 (Red)
5	СР	Clamp gate	18	OS2	Output signal 2 (Green or B/W)
6	SS	Ground	17	OS1	Output signal 1 (Blue or B/W)
7	NC	Non connection	16	SS	Ground
8	SW2	Switch gate 2 for Hi/Lo amplifier gain	15	φ2D	Transfer clock (phase 2) for B/W
9	ф2А	Transfer clock (phase 2) for color	14	φ1D	Transfer clock (phase 1) for B/W
10	φ1Α	Transfer clock (phase 1) for color	13	SH3	Shift gate 3 for B/W
11	SH1	Shift gate 1 for color	12	SH2	Shift gate 2 for B/W

Arrangement of 1st Effective Pixel (S1)





Optical/Electrical Characteristics (Color 600 dpi, High Gain Mode) Ta = 25°C, Vod = 10 V, V $_{\phi}$ = Vsh = Vrs = Vcp = 3.3 V (pulse), f $_{\phi}$ = 2.5 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1.0 mm)

(Characteristics		Symbol	Min	Тур.	Max	Unit	Note
	Red	Red Green		17.1	24.5	31.8		
Sensitivity	Green			18.7	26.7	34.7	V/lx·s	(Note 2)
	Blue		R _B	11.1	15.9	20.7		
		PRNU (1)	_	10	20	%	(Note 3-1)	
Photo response no	in uniformity		PRNU (3)	_	3	12	mV	(Note 4)
Saturation output v	oltage		VSAT	2.0	2.2	_	V	(Note 6)
Saturation exposur	e		SE	0.06	0.08	_	lx⋅s	(Note 7)
Total transfer efficiency		TTE	92	99	_	%	_	
Output impedance		ZO	_	66	250	Ω	_	
Random noise			N _{Dσ}	_	1.9	_	mV	(Note 11)

Optical/Electrical Characteristics (Color 600 dpi, Low Gain Mode) Ta = 25°C, Vod = 10 V, V $_{\phi}$ = Vsh = Vrs = Vcp = 3.3 V (pulse), f $_{\phi}$ = 2.5 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1.0 mm)

Charac	teristics	Symbol	Min	Тур.	Max	Unit	Note
	Red	R _R	11.6	16.6	21.6		
Sensitivity	Green	Rg	12.6	18.0	23.4	V/Ix·s	(Note 2)
	Blue	RB	7.5	10.6	13.8		
		PRNU (1)	_	10	20	%	(Note 3-2)
Photo response non unifo	orrinty	PRNU (3)	_	3	12	mV	(Note 4)
Saturation output voltage		VSAT	1.7	1.9	_	V	(Note 6)
Saturation exposure		SE	0.07	0.11	_	lx⋅s	(Note 7)
Total transfer efficiency		TTE	92	99	_	%	_
Output impedance		ZO	_	66	250	Ω	_
Random noise		$N_{D\sigma}$	_	1.3	_	mV	(Note 11)



Optical/Electrical Characteristics (Color 1200 dpi, High Gain Mode) Ta = 25°C, Vod = 10 V, V $_{\phi}$ = Vsh = Vrs = Vcp = 3.3 V (pulse), f $_{\phi}$ = 2.5 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1.0 mm)

Charact	eristics	Symbol	Min	Тур.	Max	Unit	Note
	Red	R _R	8.6	12.2	15.9		
Sensitivity	Green	R _G	9.4	13.4	17.4	V/lx·s	(Note 2)
	Blue	R _B	5.6	5.6 7.9 10.3			
Disability of the second of th		PRNU (1)	_	10	20	%	(Note 3-3)
Photo response non unifo	Photo response non uniformity		_	3	12	mV	(Note 4)
Register imbalance		RI	_	1.3	_	%	(Note 5)
Saturation output voltage		VSAT	1.00	1.42	_	V	(Note 6)
Saturation exposure		SE	0.06	0.11	_	lx⋅s	(Note 7)
Dark signal voltage		VDRK	_	0.6	2.0	mV	(Note 9)
Dark signal non uniformity	/	DSNU	_	4.2	10.0	mV	(Note 8)
DC power dissipation		PD	_	432	578	mW	(Note 9)
Total transfer efficiency		TTE	92	99	_	%	_
Output impedance	t impedance		_	66	250	Ω	_
DC output signal voltage		Vos	4.0	5.0	6.0	V	(Note 10)
Reset noise		VRSN	_	0.4	_	V	(Note 10)
Random noise		N _{Dσ}	_	2.1	_	mV	(Note 11)

Optical/Electrical Characteristics (Color 1200 dpi, Low Gain Mode) Ta = 25°C, VoD = 10 V, V $_{\phi}$ = VsH = Vrs = VcP = 3.3 V (pulse), f $_{\phi}$ = 2.5 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1.0 mm)

Charact	eristics	Symbol	Min	Тур.	Max	Unit	Note
	Red	RR	5.8	8.3	10.8		
Sensitivity	Green	RG	6.3	9.0	11.7	V/lx·s	(Note 2)
	Blue	RB	3.7	5.3	6.9		
Dheta ranana nan unifarmitu		PRNU (1)	_	10	20	%	(Note 3-4)
Photo response non uniformity		PRNU (3)	_	3	12	mV	(Note 4)
Register imbalance		RI	_	1.1	_	%	(Note 5)
Saturation output voltage		VSAT	0.85	0.95	_	V	(Note 6)
Saturation exposure	Saturation exposure		0.07	0.11	_	lx⋅s	(Note 7)
Dark signal voltage		VDRK	_	0.4	2.0	mV	(Nata 0)
Dark signal non uniformity	,	DSNU	_	2.8	10.0	mV	(Note 8)
DC power dissipation		PD	_	418	578	mW	(Note 9)
Total transfer efficiency		TTE	92	99	_	%	_
Output impedance	Output impedance		_	66	250	Ω	_
DC output signal voltage		Vos	3.9	4.9	5.9	V	(Note 40)
Reset noise		V _{RSN} — 0.4 —		V	(Note 10)		
Random noise		$N_{D\sigma}$		1.3		mV	(Note 11)



Optical/Electrical Characteristics (B/W 1200 dpi, High Gain Mode) Ta = 25°C, Vod = 10 V, V $_{\phi}$ = Vsh = Vrs = Vcp = 3.3 V (pulse), f $_{\phi}$ = 5.0 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1.0 mm)

Characteristics	Symbol	Min	Тур.	Max	Unit	Note
Sensitivity	R _{B/W}	25.8	36.8	47.9	V/Ix·s	(Note 2)
Dhoto roonono non uniformita	PRNU (1)	_	10	20	%	(Note 3-1)
Photo response non uniformity	PRNU (3)	_	3	12	mV	(Note 4)
Saturation output voltage	VSAT	2.0	2.2	_	V	(Note 6)
Saturation exposure	SE	0.04	0.06	_	lx⋅s	(Note 7)
Dark signal voltage	VDRK	_	1.1	2.0	mV	(Nata 0)
Dark signal non uniformity	DSNU	_	4.5	10.0	mV	(Note 8)
DC power dissipation	PD	_	407	578	mW	(Note 9)
Total transfer efficiency	TTE	92	99	_	%	_
Output impedance	ZO	_	66	250	Ω	_
DC output signal voltage	Vos	4.0	5.0	6.0	V	(Note 10)
Reset noise	VRSN	_	0.4	_	V	(Note 10)
Random noise	N _{Dσ}	_	1.8	_	mV	(Note 11)

Optical/Electrical Characteristics (B/W 1200 dpi, Low Gain Mode) Ta = 25°C, VoD = 10 V, V $_{\phi}$ = VsH = Vrs = VcP = 3.3 V (pulse), f $_{\phi}$ = 5.0 MHz, frs = 5.0 MHz, tint (integration time) = 11 ms, light source = A light source + CM500S (t = 1 mm)

Characteristics	Symbol	Min	Тур.	Max	Unit	Note
Sensitivity	R _{B/W}	17.3	24.7	32.1	V/Ix·s	(Note 2)
Dhata assault assault assault a	PRNU (1)	_	10	20	%	(Note 3-1)
Photo response non uniformity	PRNU (3)	_	3	12	mV	(Note 4)
Saturation output voltage	VSAT	1.7	1.9	_	V	(Note 6)
Saturation exposure	SE	0.05	0.07	_	lx⋅s	(Note 7)
Dark signal voltage	VDRK	_	0.7	2.0	mV	(Note 9)
Dark signal non uniformity	DSNU	_	2.8	10.0	mV	(Note 8)
DC power dissipation	PD	_	394	578	mW	(Note 9)
Total transfer efficiency	TTE	92	99	_	%	_
Output impedance	ZO	_	66	250	Ω	_
DC output signal voltage	Vos	3.9	4.9	5.9	V	(Nata 40)
Reset noise	V _{RSN}	_	0.4	_	V	(Note 10)
Random noise	N _{Dσ}	_	1.2	_	mV	(Note 11)



- Note 2: Sensitivity is defined for each color of signal outputs average when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.
- Note 3-1: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, where measured approximately 1000 mV of signal output.

PRNU (1) =
$$\frac{\Delta X}{\overline{X}} \times 100$$
 (%)

 \overline{X} : Average of total signal outputs

 ΔX : The maximum deviation from \overline{X}

Note 3-2: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, where measured approximately 800 mV of signal output.

PRNU (1) =
$$\frac{\Delta X}{\overline{X}} \times 100 \text{ (%)}$$

 $\overline{\mathbf{X}}$: Average of total signal outputs

 ΔX : The maximum deviation from \overline{X}

Note 3-3: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, where measured approximately 500 mV of signal output.

PRNU (1) =
$$\frac{\Delta X}{\overline{X}} \times 100 \text{ (%)}$$

 \overline{X} : Average of total signal outputs

 ΔX : The maximum deviation from \overline{X}

Note 3-4: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature, where measured approximately 400 mV of signal output.

PRNU (1) =
$$\frac{\Delta X}{\overline{X}} \times 100$$
 (%)

 \overline{X} : Average of total signal outputs

 ΔX : The maximum deviation from \overline{X}

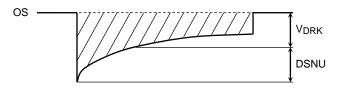
- Note 4: PRNU (3) is defined as the maximum voltage with next pixel, where measured approximately 50 mV of signal output.
- Note 5: Register imbalance is defined as follows.

- Note 6: VSAT is defined as the minimum saturation output voltage of all effective pixels. Condition is over exposure situation and VOD = 9.5 V.
- Note 7: Definition of SE:

$$SE(B/W) = \frac{VSAT}{RB/W} \qquad SE(Color) = \frac{VSAT}{RG}$$

Note 8: VDRK is defined as average dark signal voltage of all effective pixels.

DSNU is defined by the difference between average value (VDRK) and the maximum value of the dark voltage.





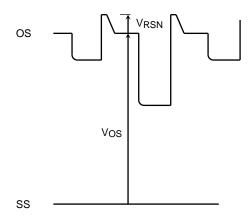
Note 9: PD is defined as follows. IOD is DC current dissipation.

$$PD = VOD \times IOD$$

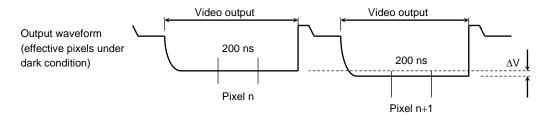
Measurement condition is VOD = 10.5 V and input pulse voltage = 5.5 V.

Note 10: DC output signal voltage is defined as follows.

Reset noise voltage is defined as follows.



Note 11: Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure. CP pulse width: 50 ns



- 1) Two adjacent pixels (pixel n and n+1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output periods averaged over 200 ns period to get V(n) and V(n+1).
- 3) V(n+1) is subtracted from V(n) to get ΔV .

$$\Delta V = V(n) - V(n+1)$$

4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} \! \left| \Delta V_i \right| \qquad \qquad \sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} \! \left(\! \left| \Delta V_i \right| - \overline{\Delta V} \right)^2}$$

- 5) Procedure 2), 3) and 4) are repeated 10 times to get sigma value.
- 6) 10 sigma values are averaged.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

7) $\bar{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as follows.

$$ND_{\sigma} = \frac{1}{\sqrt{2}}\bar{\sigma}$$



Recommended Operating Conditions (Ta = 25°C)

For best performance, the device should be used within the Recommended Operating Conditions.

Characteristics	i	Symbol	Min	Тур.	Max	Unit	
Clock pulse velters	"H" level	$V_{\varphi 1A},V_{\varphi 2A}$	3.1	3.3	5.5	V	
Clock pulse voltage	"L" level	$V_{\phi 1D}, V_{\phi 2D}$	0	0	0.1	V	
Last stage clock pulse	"H" level		3.1	3.3	5.5	V	
voltage	"L" level	$V_{\phi 1B}, V_{\phi C}, V_{\phi 1D^*}$	0	0	0.1	V	
Chift pulse veltage	"H" level	Vari	2.7	3.3	5.5	V	
Shift pulse voltage	"L" level	VSH	0	0	0.8	V	
Deact pulse valtage	"H" level	\/	3.1	3.3	5.5	V	
Reset pulse voltage	"L" level	VRS	0	0	0.5	V	
Clamp pulse veltage	"H" level	V	3.1	3.3	5.5	V	
Clamp pulse voltage	"L" level	VCP	0	0	0.5	V	
Switch pulse veltage	"H" level	Van	2.7	3.3	5.5	V	
Switch pulse voltage	"L" level	Vsw	0	0	0.8	V	
Power supply voltage		V _{OD}	9.5	10.0	10.5	V	

Clock Characteristics (Ta = 25°C)

For best performance, the device should be used within the Recommended Operating Conditions.

Characteristics		Symbol	Min	Тур.	Max	Unit
Clock pulse frequency		f_{φ}	2.5	2.5	35.0	MHz
Reset pulse frequency		fRS	5.0	5.0	35.0	MHz
Clamp pulse frequency		fCP	5.0	5.0	35.0	MHz
Clock (1A) capacitance for Color	(Note 12)	C _{∮1} A	_	163	_	pF
Clock (2A) capacitance for Color	(Note 12)	C _{ф2} A	_	165	_	pF
Last stage clock capacitance	(Note 12)	С _{ф1В,} С _ф С, С _{ф1D*}	_	6	_	pF
Clock (1D) capacitance for B/W	(Note 12)	C _{ϕ1D}	_	72	_	pF
Clock (2D) capacitance for B/W	(Note 12)	C _{\phi} 2D	_	73	_	pF
Shift gate (SH1) capacitance for Color		C _{SH1}	_	14	_	pF
Shift gate (SH2) capacitance for B/W		CSH2	_	14	_	pF
Shift gate (SH3) capacitance for B/W		C _{SH3}	_	5.3	_	pF
Reset gate capacitance		C _{RS}	_	7	_	pF
Clamp gate capacitance		ССР	_	6	_	pF
Switch gate capacitance		C _{SW}	_	13		pF

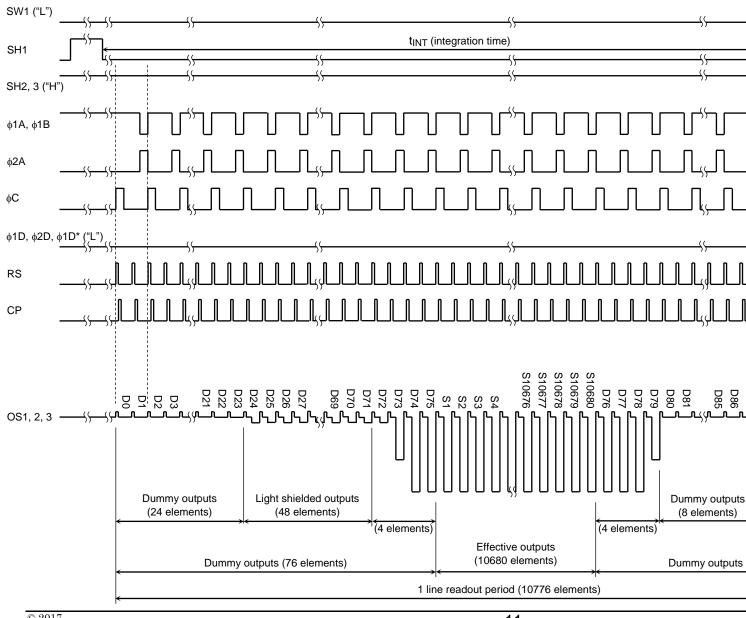
Note 12: Vop = 10 V, Input capacitance per a pin.



Clocking Mode

	Mod	de		SW1	SW2	SH1	SH2	SH3	φ1A, φ2A	ф1В	φС	φ1D, φ2D	φ1D*	RS	СР	
Color Low		High	1200 dpi	"L"	"H"	Pulse	"1	1 "	Pulse	ф1А	Pulse	"L	"	Pulse	Pulse	
		600 dpi	L		Puise	"H"		"H"		Puise	φ′	IA	L	-	Puise	Puise
	1200 dpi	"] "	""	"L" Pulse		"H"		"11"		ф1А	Pulse	"L	"	Pulse	Pulse	
Bi clamp	Bi clamp	gain 600 dpi						φ′	IA		-	ruise	Fuise			
/ Line clamp		High	1200 dpi	"H"	H" "H"	"H"	Pulse	Pulse		"L"		Pu	lse	Pulse	Pulse	
	gain	gain	600 dpi	П			Pu	Pulse		L		Pu	lse	ruise	Fuise	
	B/W Low		1200 dpi	"H"	"1" "1"		Pulse	Pulse		"L"		Pu	lse	Pulse	Pulco	
	gain		600 dpi	П	<u> </u>	"L" "H"		lse	- "L"		Pu	lse	ruise	Pulse		

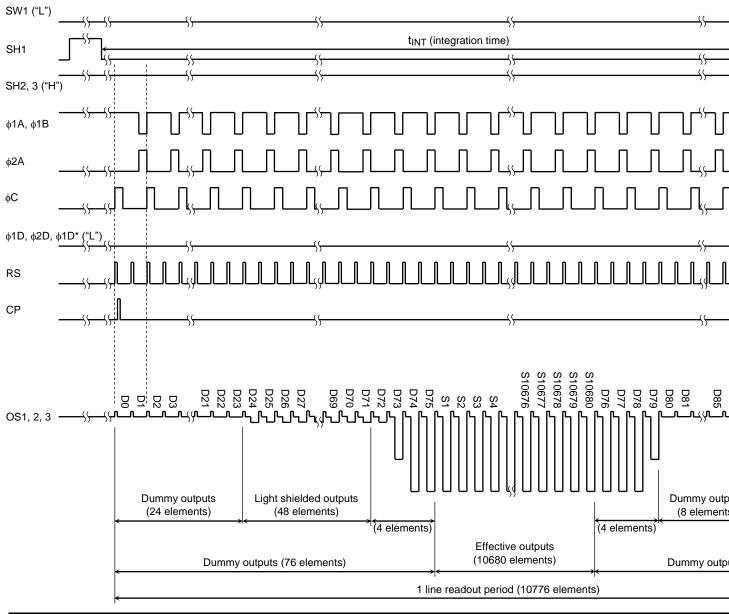
Timing Chart 1: Color 1200 dpi Mode (Bit Clamp Mode)



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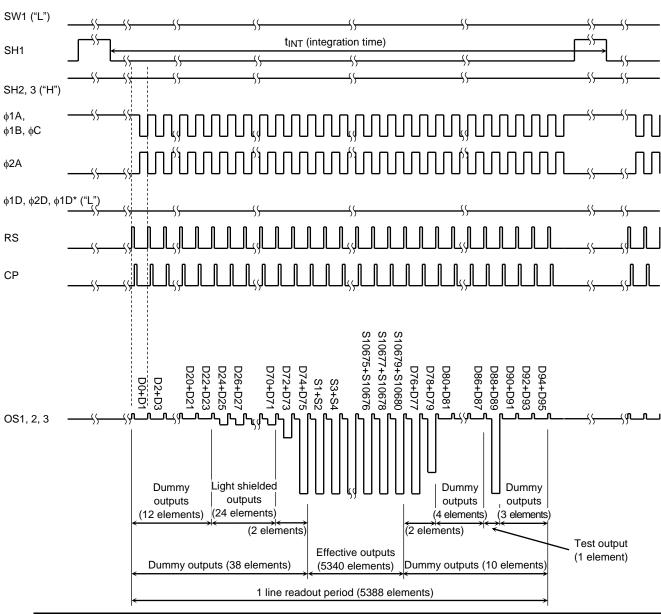
Timing Chart 2: Color 1200 dpi Mode (Line Clamp Mode)



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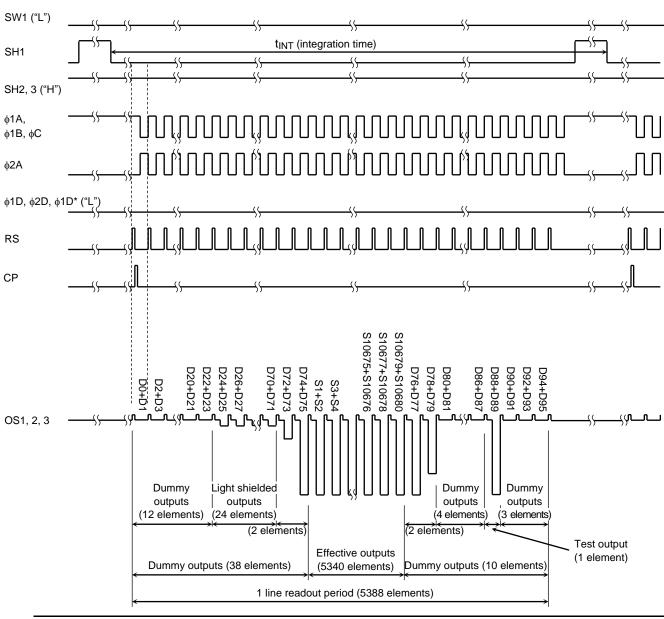
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Timing Chart 3: Color 600 dpi Mode (Bit Clamp Mode)

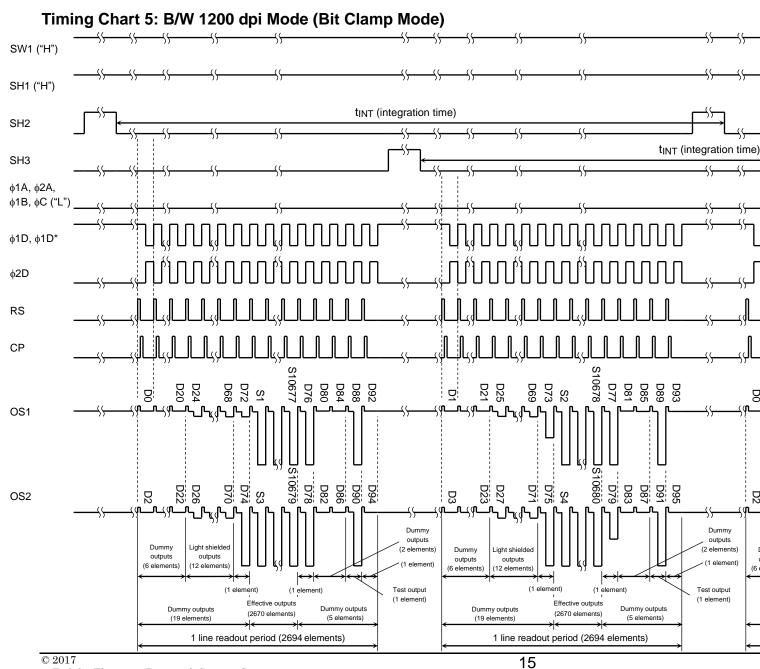


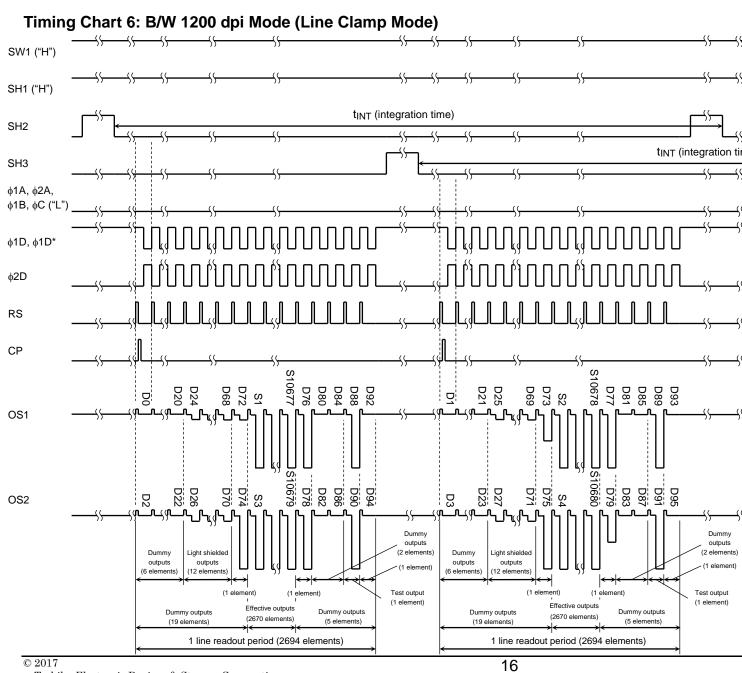
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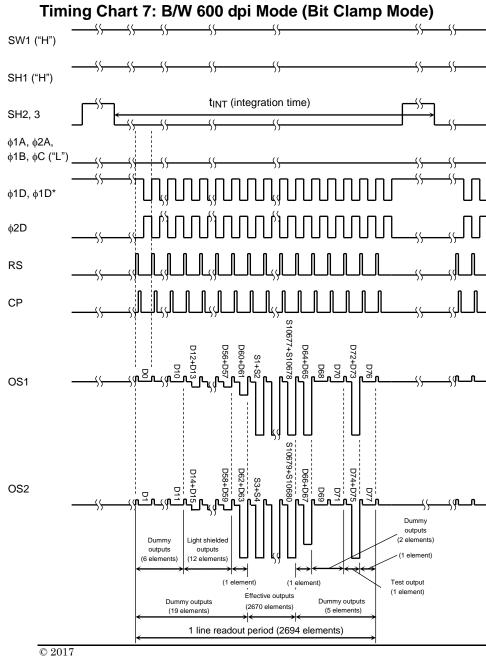
Timing Chart 4: Color 600 dpi Mode (Line Clamp Mode)



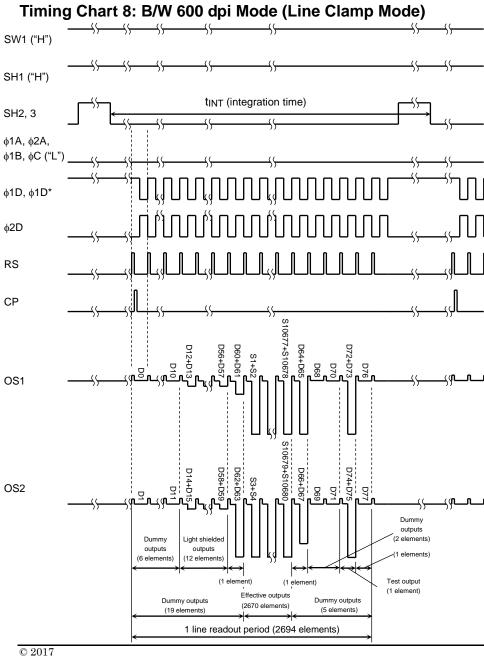
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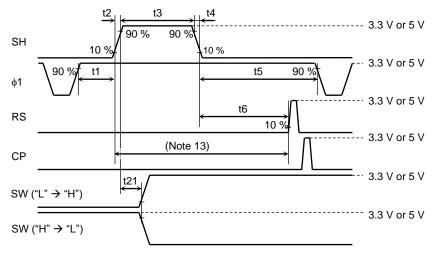
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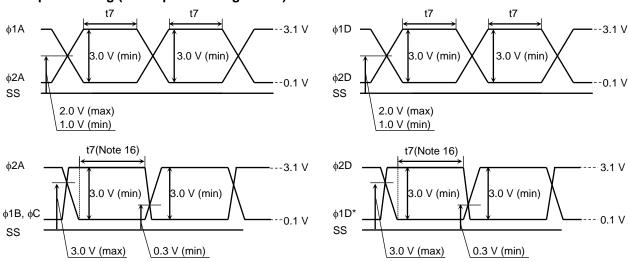


Timing Requirements



Note 13: Keep the RS and CP pins "L" level.

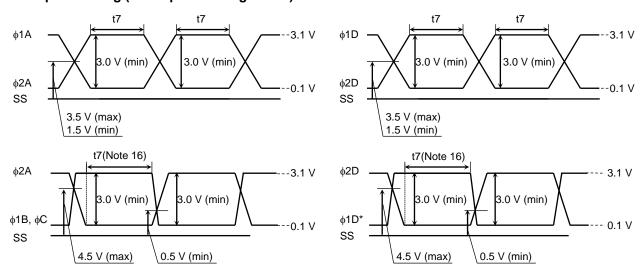
Cross point timing (Clock pulse voltage 3.3 V)



Note 16: Pulse width is the period when voltage difference between $\phi 2A$ and $\phi 1B/\phi C$, $\phi 2D$ and $\phi 1D^*$ is over 3.0 V. Observe the specification strictly because of normal transfer efficiency.

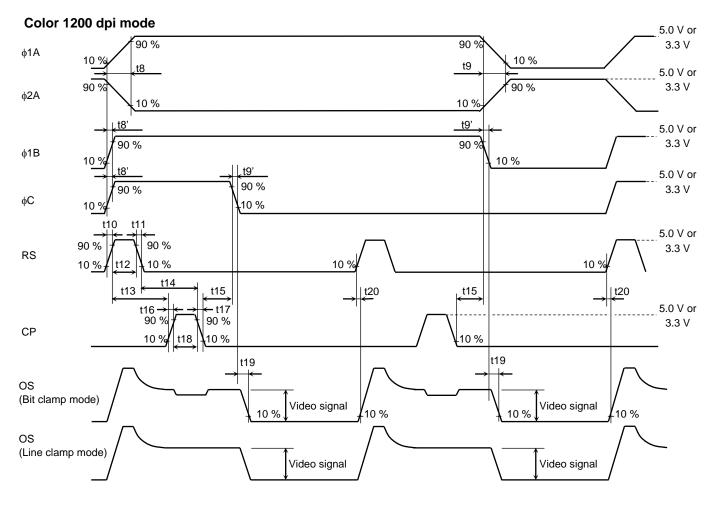
Cross point timing (Clock pulse voltage 5.0 V)

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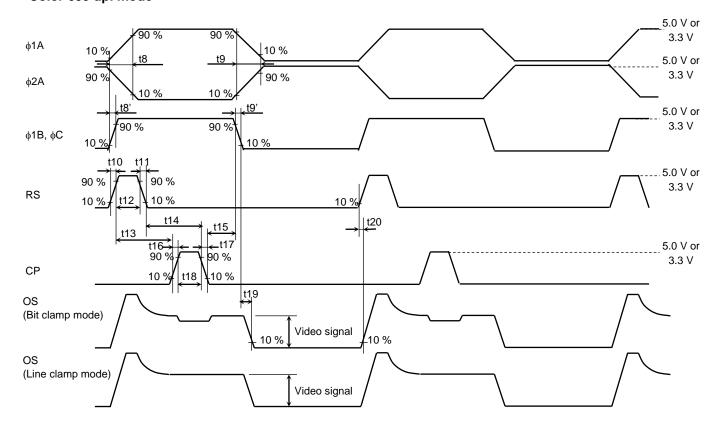


Note 16: Pulse width is the period when voltage difference between $\phi 2A$ and $\phi 1B/\phi C$, $\phi 2D$ and $\phi 1D^*$ is over 3.0 V. Observe the specification strictly because of normal transfer efficiency.



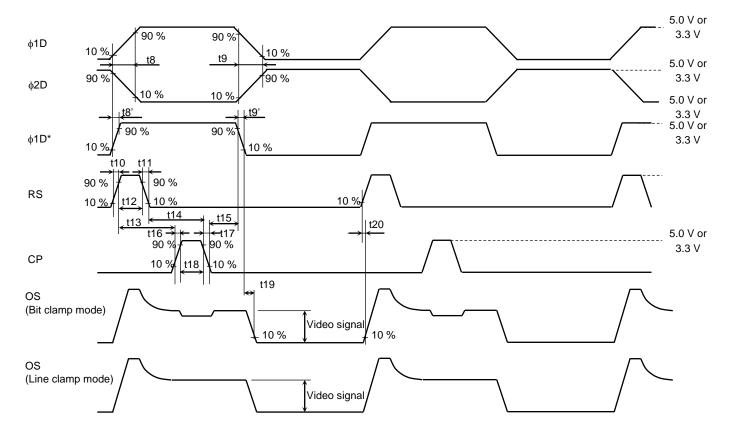


Color 600 dpi mode





B/W 1200 dpi mode & B/W 600 dpi mode (SH2 = SH3)





Charac	eteristics	Symbol	Min	Typ. (Note 14)	Max	Unit
Dulga timing of CLL and	14	t1	120	200	2500	ns
Pulse timing of SH and	p I	t5	1000	1075	2500	ns
SH pulse rise time, fall ti	me	t2, t4	0	10	_	ns
SH pulse width	pulse width		3000	3500	_	ns
Pulse timing of SH and I	RS	t6	975	_	_	ns
φ1A, φ2A pulse width	(Note 15)					
φ1D, φ2D pulse width	(Note 15)	17	0	00		
φ2A, φ1B/ φC pulse widt	h (Note 16)	t7	6	90	_	ns
φ2D, φ1D* pulse width	(Note 16)					
φ1A, φ2A pulse rise time	, fall time	10.10	0	45		
φ1D, φ2D pulse rise time	e, fall time	t8, t9	0	15	_	ns
φ1B, φC, φ1D* pulse rise	time, fall time	t8', t9'	0	3	8	ns
RS pulse rise time, fall ti	me	t10, t11	0	10	_	ns
RS pulse width		t12	6	15	_	ns
D. I (DO 14	25	t13	0	0	_	ns
Pulse timing of RS and 0	JP .	t14	6	50	_	ns
Pulse timing of \$1B and	СР					
Pulse timing of	CP CP	t15	-2	40	_	ns
Pulse timing of \$1D* and	d CP					
CP pulse rise time, fall ti	me	t16, t17	0	10	_	ns
CP pulse width		t18	6	40	_	ns
	φ1B and OS		_	8.5	_	ns
Video dete delevido	φC and OS	t19	_	8.5	_	ns
Video data delay time	φ1D* and OS		_	8.5	_	ns
	RS and OS	t20	_	3.1	_	ns
Pulse timing of SH and S	SW	t21	100	500	t3-100	ns

Note 14: Measured with fRS = 5 MHz.

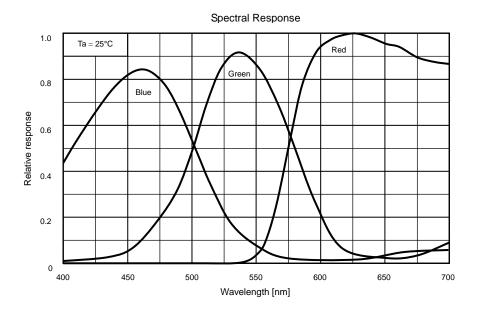
22

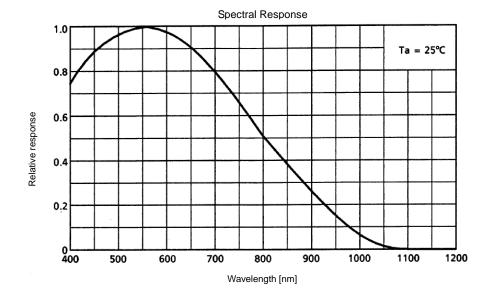
Note 15: Pulse width is the period when voltage difference between $\phi 1A$ and $\phi 2A$, $\phi 1D$ and $\phi 2D$ is over 3.0 V. Observe the specification strictly because of normal transfer efficiency.

Note 16: Pulse width is the period when voltage difference between $\phi 2A$ and $\phi 1B/\phi C$, $\phi 2D$ and $\phi 1D^*$ is over 3.0 V. Observe the specification strictly because of normal transfer efficiency.



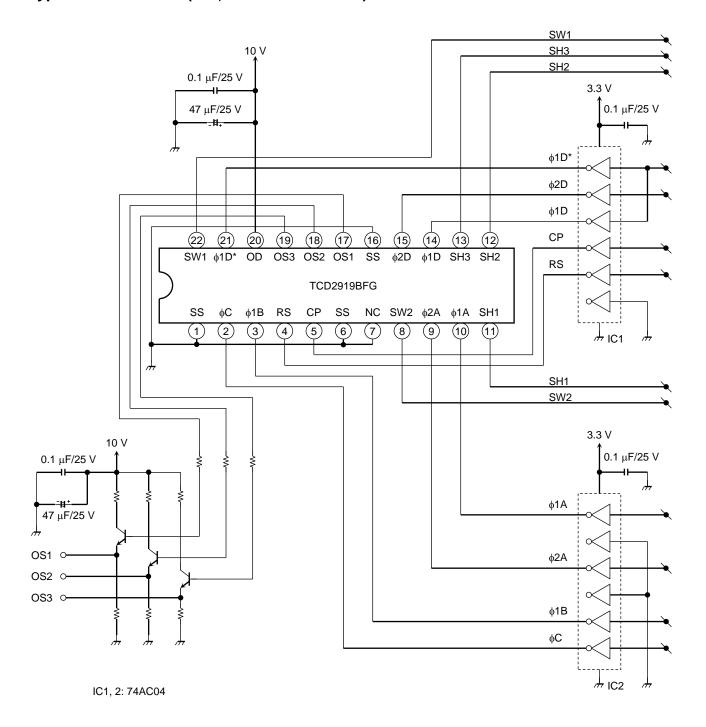
Typical Spectral Response





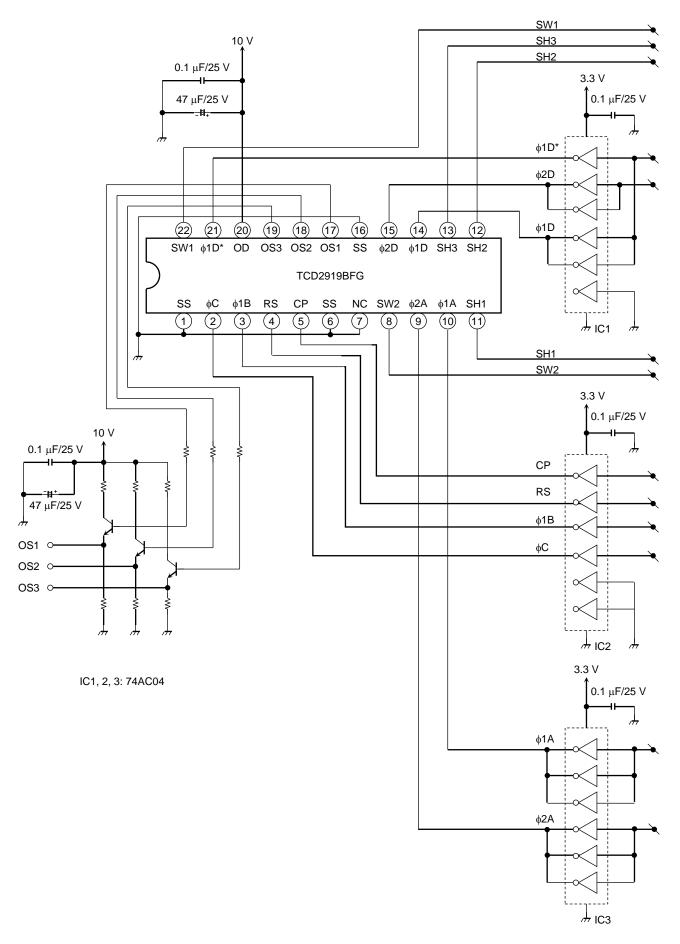


Typical Drive Circuit (at $f_{\phi} = 15$ MHz or lower)





Typical Drive Circuit





Cautions

1. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

CCD Image Sensor is protected against static electricity, but inferior puncture mode device due to static electricity is sometimes detected. In handing the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

- Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.
- Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.
- c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.
- d. Ionized air is recommended for discharge when handling CCD image sensors.

It is not necessarily required to execute all precaution items for static electricity.

It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

2. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

3. Cloudiness of Glass Inside

CCD surface mount products may have a haze on the inside of glass, so be careful about following. Even if the haze arises inside of glass, when it is not on the pixel area, there is no problem in quality. Before the aluminum bag is opened, please keep the products in the environment below 30°C·90 %RH. And after the aluminum bag is opened, please keep the products in the environment below 30°C·60 %RH. Please mount the products within 12 months from sealed date and within 6 months from opening the aluminum bag. (Sealed date is printed on aluminum bag.)

4. Ultrasonic Cleaning

Ultrasonic cleaning should not be used with such hermetically-sealed ceramic package as CCD because the bonding wires can become disconnected due to resonance during the cleaning process.

5. Mounting

In the case of solder mounting, the devices should be mounted with the window glass protective tape in order to avoid dust or dirt included in reflow machine.

6. Window Glass Protective Tape

The window glass protective tape is manufactured from materials in which static charges tend to build up. When removing the tape from CCD sensor after solder mounting, install an ionizer to prevent the tape from being charged with static electricity.

When the tape is removed, adhesives will remain in the glass surface. Since these adhesives appear as black or white flaws on the image, please wipe the window glass surface with the cloth into which the organic solvent was infiltrated. Then please attach CCD to a product.

Do not reuse the tape.



7. Soldering Temperature Profile

Good temperature profile for each soldering method is as follows. In addition, in case of the repair work accompanied by IC removal, since the degree of parallel may be spoiled with the left solder, please do not carry out and in case of the repair work not accompanied by IC removal, carry out with a soldering iron or , in reflow, only one time.

- a. Using a soldering iron
 - Complete soldering within three seconds for lead temperatures of up to 350°C.
- b. Using long infrared rays reflow / hot air reflow

Please do reflow at the condition that the package surface (electrode) temperature is on the solder maker's recommendation profile. And that reflow profile is within below condition 1 to 3.

- 1. Peak temperature: 250°C or less.
- 2. Time to keep high temperature: 220 to 250°C, 30 to 40 s.
- 3. Pre. heat: 150 to 190°C, 60 to 120 s

8. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

9. Cleaning Method of the Window Glass Surface

Wiping Cloth

- a. Use soft cloth with a fine mesh.
- b. The wiping cloth must not cause dust from itself.
- c. Use a clean wiping cloth necessarily.

Cleaner

When using solvents, such as alcohol, unavoidably, it is cautious of the next.

- a. A clean thing with quick-drying.
- b. After liquid dries, there needs to be no residual substance.
- c. A thing safe for a human body.

And, please observe the use term of a solvent and use the storage container of a solvent to be clean. Be cautious of fire enough.

Way of Cleaning

First, the surface of window glass is wiped with the wiping cloth into which the cleaner was infiltrated. Please wipe down the surface of window glass at least 2 times or more.

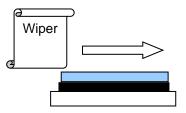
Next, the surface of window glass wipes with the dry wiping cloth. Please wipe down the surface of window glass at least 3 times or more.

Finally, blow cleaning is performed by dry N₂ filtered.

If operator wipes the surface of the window glass with the above-mentioned process and dirt still remains, TOSHIBA recommends repeating the clean operation from the beginning.

Be cautious of the next thing.

- a. Don't infiltrate the cleaner too much.
- b. A wiping portion is performed into the optical range and don't touch the edge of window glass.
- c. Be sure to wipe in a long direction and the same direction.
- A wiping cloth always uses an unused portion.

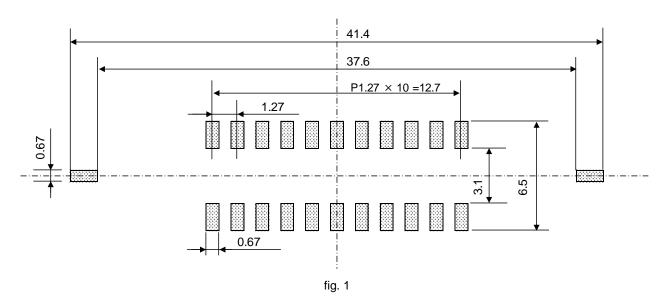




10. Foot Pattern on the PCB

We recommend fig.1 's foot pattern for your PCB(Printed Circuit Board).

Unit: mm



11. Mask for Solder Paste Application

We recommend metal mask that have the following thickness.

·Thickness: 0.2 mm.

And we recommend that the opened area size on the metal mask is 95 % to 100 % for pads on solder.

12. Temperature Cycle

After mounting, if temperature cycle stress is too much, CCD surface mount products have a possibility that a crack may arise in solder. As a method of preventing a solder crack, underfill is effective.

13. Reuse of a Tray

We reuse tray in order to reduce plastic waste as we can. Please cooperate with us in reusing for ecology.



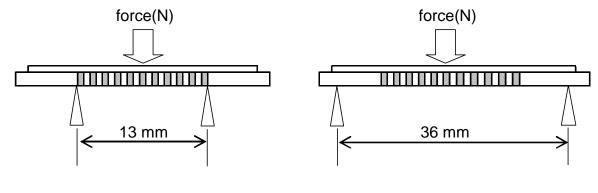
14. Caution for Package Handling

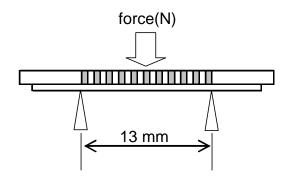
Over force on CCD products may cause crack and chip removing on the product. The three point bending strength of this product is the following. (Reference data)

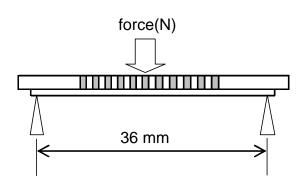
If the stress is loaded far from a fulcrum, the stress on the package will be increase.

When you will treat CCD on every process, please be careful particularly. For example, soldering on PCB, cutting PCB, wiping on the glass surface, optical assemble and so on.

Bending Test







•22CLCC

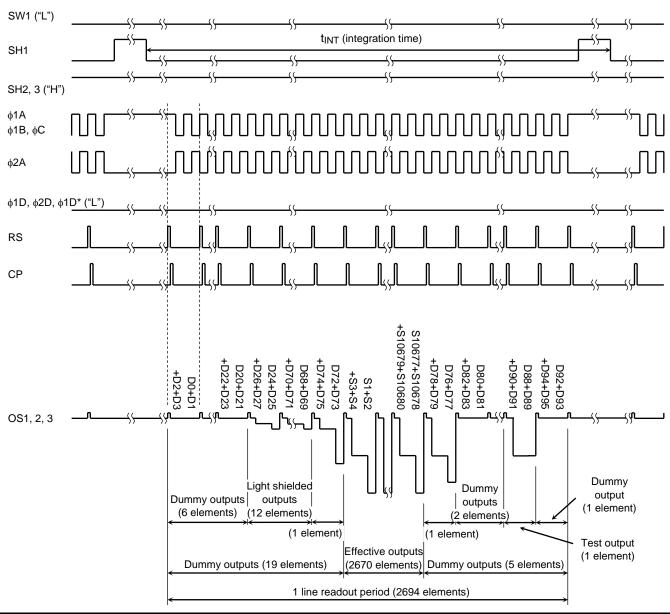
Bearing length 13 mm: The force from upside: 300 [N]

The force from downside: 200 [N]

Bearing length 36 mm: The force from upside: 150 [N]

The force from downside: 80 [N]

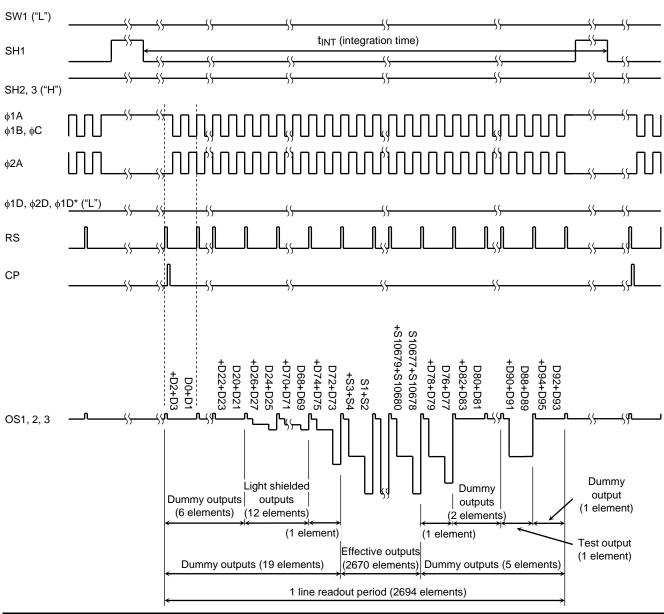
Application Note (Reference Only): Timing Chart (Color 300 dpi Mode: Bit Clamp Mode)



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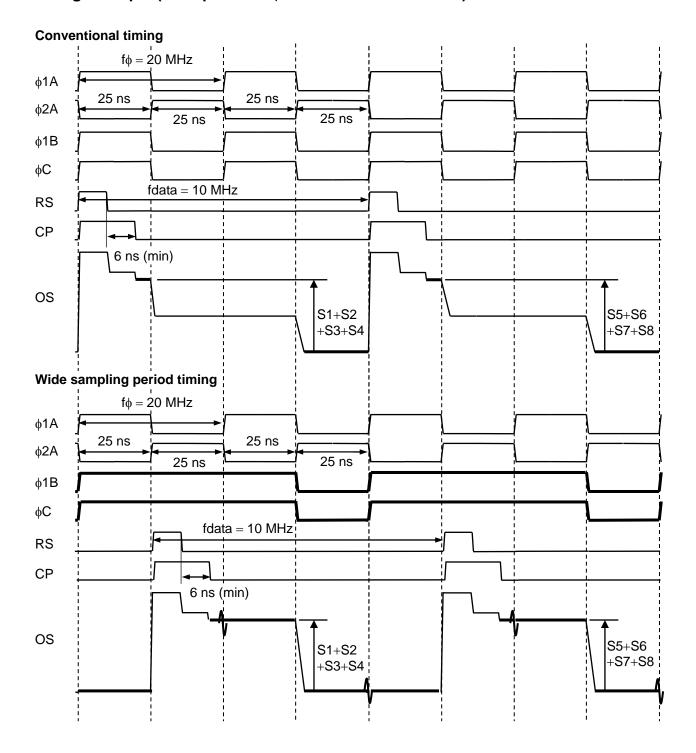
Application Note (Reference Only): Timing Chart (Color 300 dpi Mode: Line Clamp Mode)



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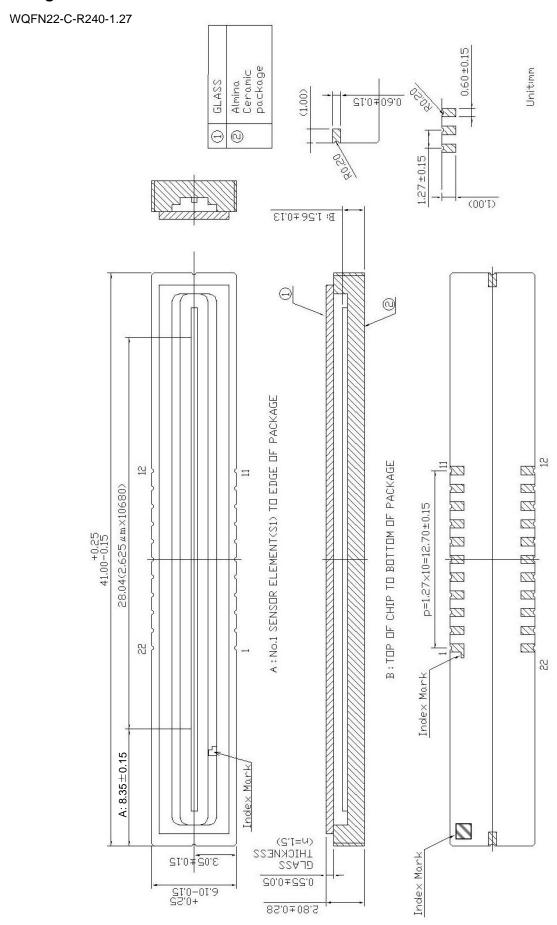


Timing Example (300 dpi Mode/ f_{ϕ} = 20 MHz/fdata = 10 MHz)





Package Dimensions





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